Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

NGTB40N120FLWG

IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for UPS and solar applications. Incorporated into the device is a soft and fast co−packaged free wheeling diode with a low forward voltage.

Features

- Low Saturation Voltage using NPT Trench with Field Stop Technology
- Low Switching Loss Reduces System Power Dissipation
- 10 μs Short Circuit Capability
- Low Gate Charge
- Soft, Fast Free Wheeling Diode
- These are Pb−Free Devices

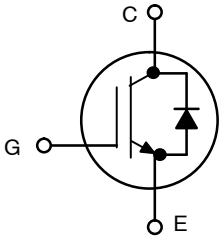
Typical Applications

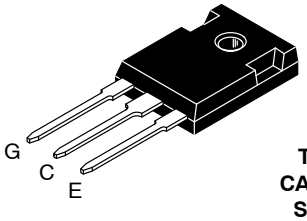
- Solar Inverter
- UPS Inverter

ON Semiconductor®

http://onsemi.com

40 A, 1200 V
V_{CEsat} = 2.0 V
E_{off} = 1.6 mJ





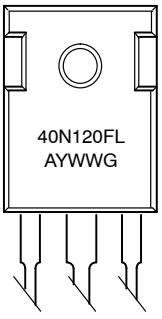
TO−247
CASE 340L
STYLE 4

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−emitter voltage	V_{CES}	1200	V
Collector current @ T_C = 25°C @ T_C = 100°C	I_C	 80 40	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	160	A
Diode forward current @ T_C = 25°C @ T_C = 100°C	I_F	 80 40	A
Diode pulsed current, T_{pulse} limited by T_{Jmax}	I_{FM}	160	A
Gate−emitter voltage Transient gate−emitter voltage (T_{pulse} = 5 μs, D < 0.10)	V_{GE}	±20 ±25	V
Power Dissipation @ T_C = 25°C @ T_C = 100°C	P_D	 260 104	W
Short Circuit Withstand Time V_{GE} = 15 V, V_{CE} = 500 V, $T_J \le$ 150°C	T_{SC}	10	μs
Operating junction temperature range	T_J	−55 to +150	°C
Storage temperature range	T_{stg}	−55 to +150	°C
Lead temperature for soldering, 1/8” from case for 5 seconds	T_{SLD}	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB40N120FLWG	TO−247 (Pb−Free)	30 Units / Rail

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction−to−case, for IGBT	$R_{\theta JC}$	0.48	°C/W
Thermal resistance junction−to−case, for Diode	$R_{\theta JC}$	1.5	°C/W
Thermal resistance junction−to−ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
STATIC CHARACTERISTIC						
Collector−emitter breakdown voltage, gate−emitter short−circuited	V_{GE} = 0 V, I_C = 500 μA	$V_{(BR)CES}$	1200	−	−	V
Collector−emitter saturation voltage	V_{GE} = 15 V, I_C = 40 A V_{GE} = 15 V, I_C = 40 A, T_J = 150°C	V_{CEsat}	1.50 −	2.0 2.2	2.2 −	V
Gate−emitter threshold voltage	V_{GE} = V_{CE}, I_C = 400 μA	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector−emitter cut−off current, gate−emitter short−circuited	V_{GE} = 0 V, V_{CE} = 1200 V V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 150°C	I_{CES}	− −	− −	1.0 2	mA
Gate leakage current, collector−emitter short−circuited	V_{GE} = 20 V , V_{CE} = 0 V	I_{GES}	−	−	200	nA
DYNAMIC CHARACTERISTIC						
Input capacitance	V_{CE} = 20 V, V_{GE} = 0 V, f = 1 MHz	C_{ies}	−	10,000	−	pF
Output capacitance		C_{oes}	−	240	−	
Reverse transfer capacitance		C_{res}	−	180	−	
Gate charge total	V_{CE} = 600 V, I_C = 40 A, V_{GE} = 15 V	Q_g	−	415	−	nC
Gate to emitter charge		Q_{ge}	−	80	−	
Gate to collector charge		Q_{gc}	−	170	−	
SWITCHING CHARACTERISTIC, INDUCTIVE LOAD						
Turn−on delay time	T_J = 25°C V_{CC} = 600 V, I_C = 40 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(on)}$	−	130	−	ns
Rise time		t_r	−	41	−	
Turn−off delay time		$t_{d(off)}$	−	385	−	
Fall time		t_f	−	140	−	
Turn−on switching loss		E_{on}	−	2.6	−	mJ
Turn−off switching loss		E_{off}	−	1.6	−	
Total switching loss		E_{ts}	−	4.2	−	
Turn−on delay time	T_J = 125°C V_{CC} = 600 V, I_C = 40 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(on)}$	−	130	−	ns
Rise time		t_r	−	42	−	
Turn−off delay time		$t_{d(off)}$	−	400	−	
Fall time		t_f	−	230	−	
Turn−on switching loss		E_{on}	−	3.0	−	mJ
Turn−off switching loss		E_{off}	−	2.8	−	
Total switching loss		E_{ts}	−	5.8	−	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
DIODE CHARACTERISTIC						
Forward voltage	V_{GE} = 0 V, I_F = 40 A V_{GE} = 0 V, I_F = 40 A, T_J = 150°C	V_F	– –	2.7 3.5	3.5	V
Reverse recovery time	T_J = 25°C I_F = 40 A, V_R = 400 V di_F/dt = 200 A/μs	t_{rr}	–	200	–	ns
Reverse recovery charge		Q_{rr}	–	1.5	–	μc
Reverse recovery current		I_{rrm}	–	15	–	A
Reverse recovery time	T_J = 125°C I_F = 40 A, V_R = 400 V di_F/dt = 200 A/μs	t_{rr}	–	260	–	ns
Reverse recovery charge		Q_{rr}	–	2.0	–	μc
Reverse recovery current		I_{rrm}	–	22	–	A

TYPICAL CHARACTERISTICS

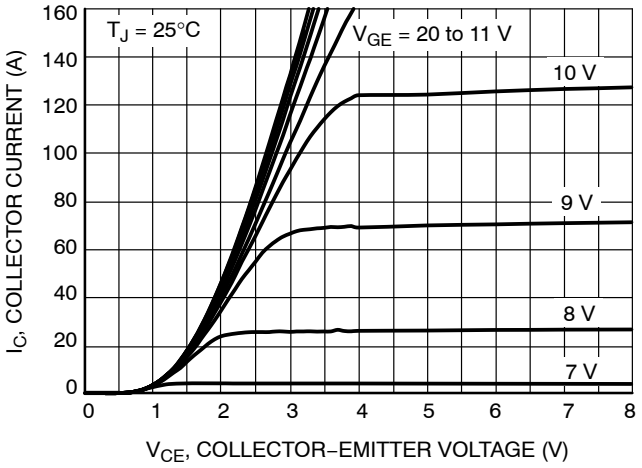


Figure 1. Output Characteristics

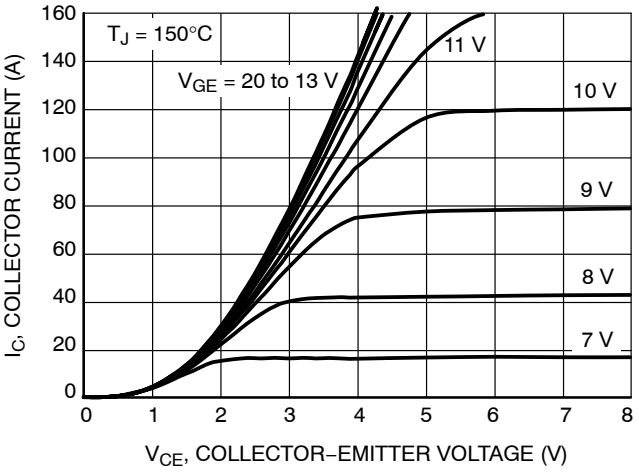


Figure 2. Output Characteristics

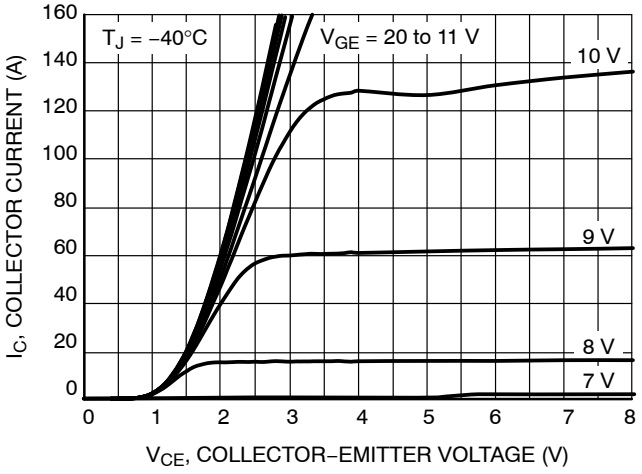


Figure 3. Output Characteristics

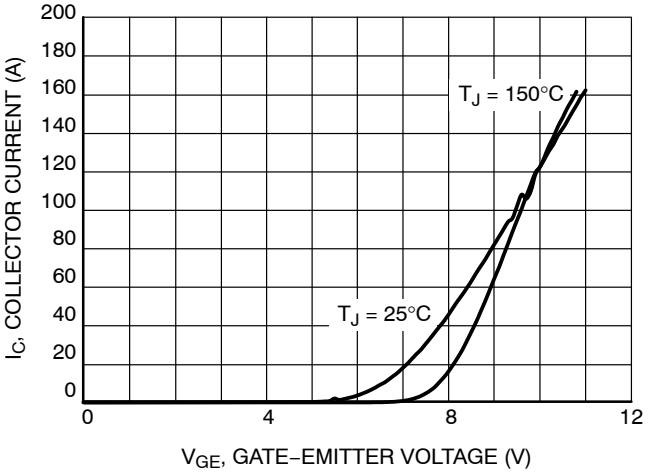


Figure 4. Typical Transfer Characteristics

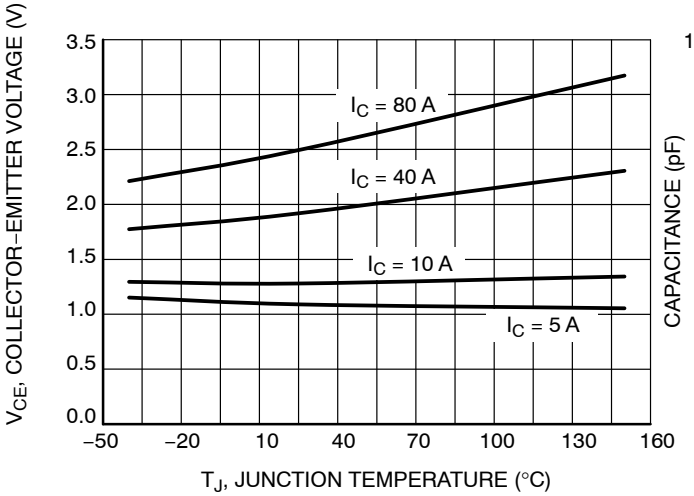


Figure 5. $V_{CE(sat)}$ vs. T_J

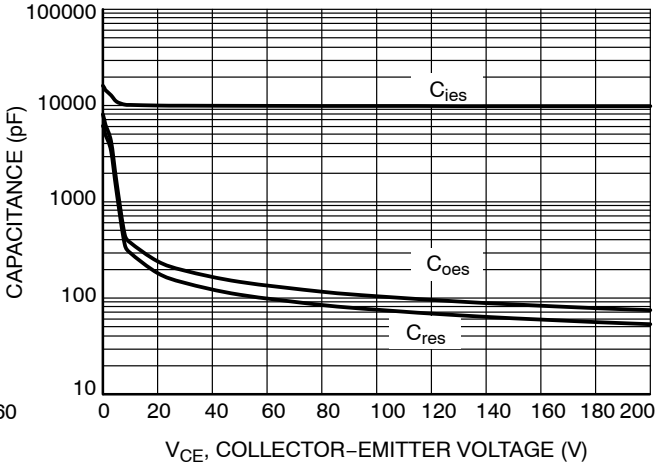


Figure 6. Typical Capacitance

TYPICAL CHARACTERISTICS

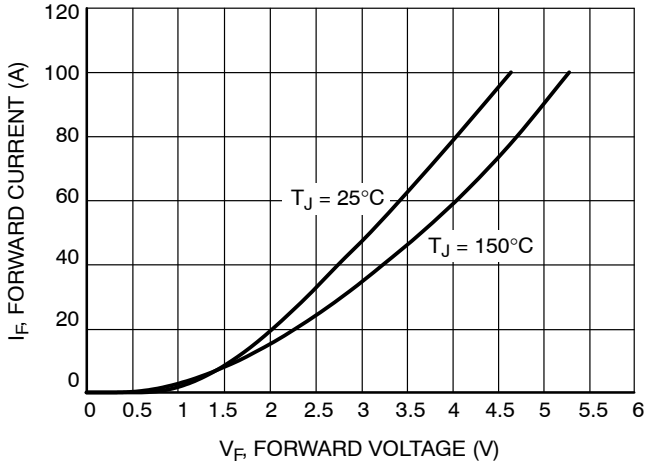


Figure 7. Diode Forward Characteristics

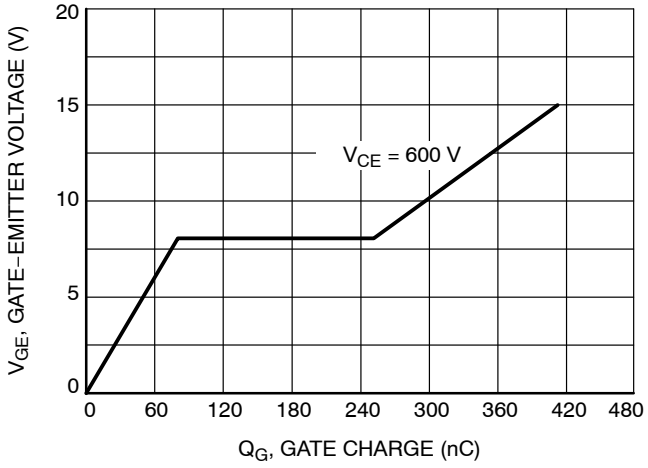


Figure 8. Typical Gate Charge

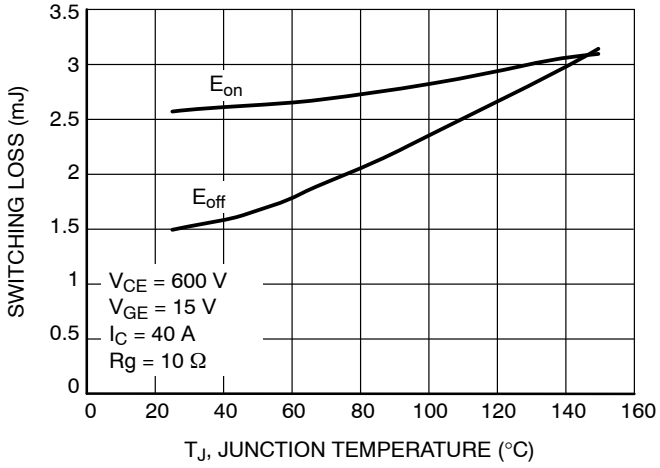


Figure 9. Switching Loss vs. Temperature

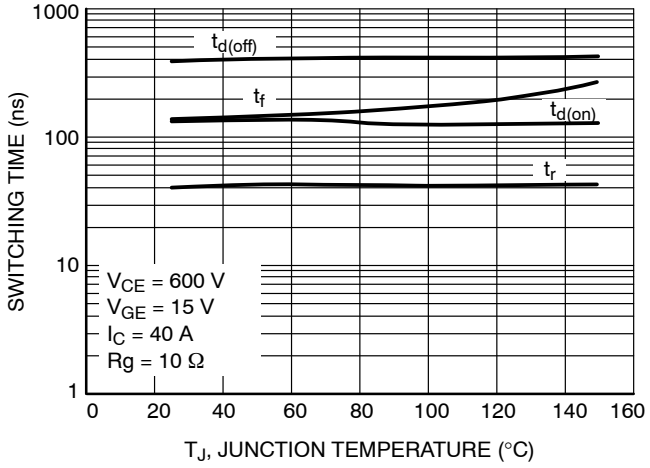


Figure 10. Switching Time vs. Temperature

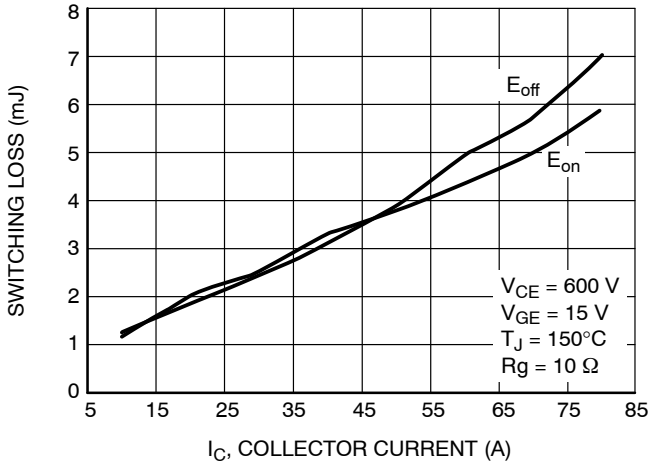


Figure 11. Switching Loss vs. I_C

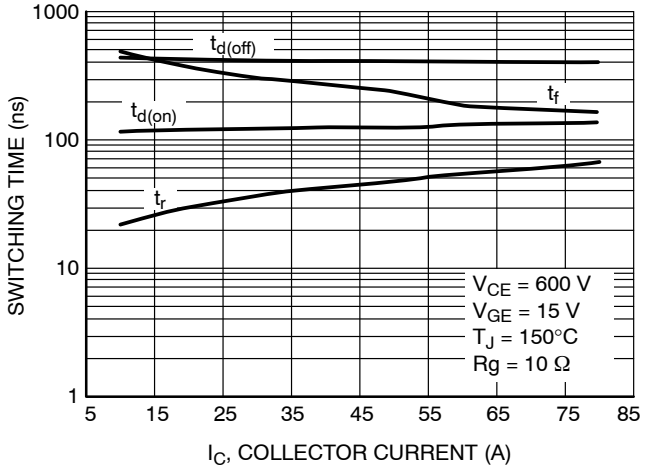


Figure 12. Switching Time vs. I_C

TYPICAL CHARACTERISTICS

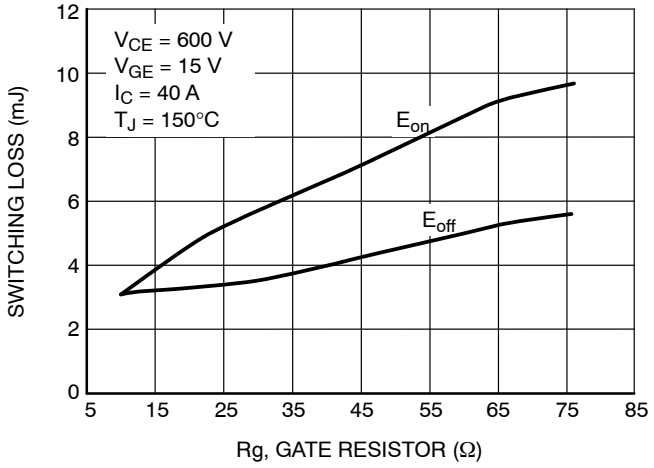


Figure 13. Switching Loss vs. Rg

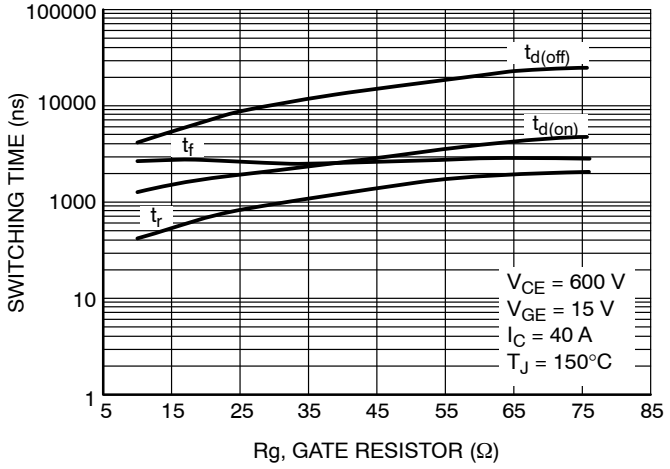


Figure 14. Switching Time vs. Rg

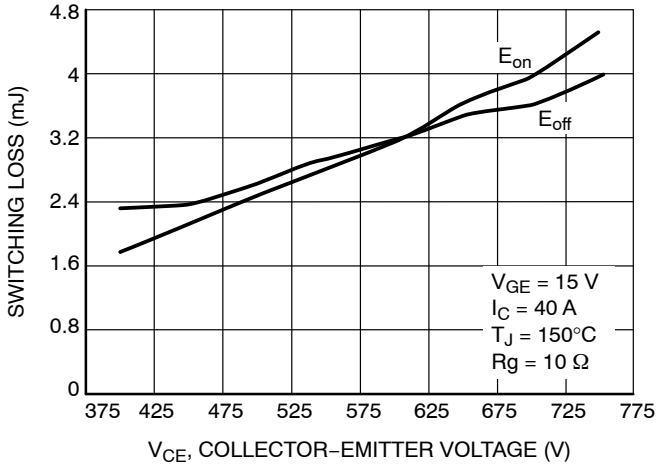


Figure 15. Switching Loss vs. V_{CE}

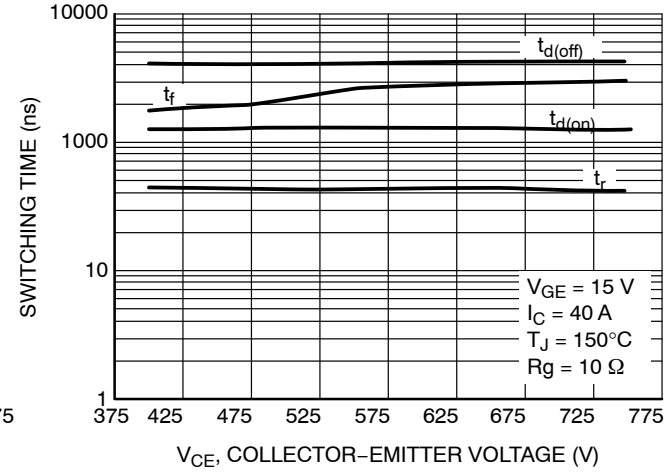


Figure 16. Switching Time vs. V_{CE}

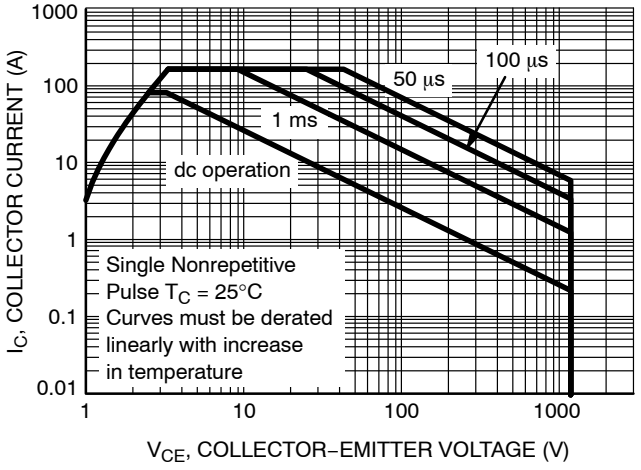


Figure 17. Safe Operating Area

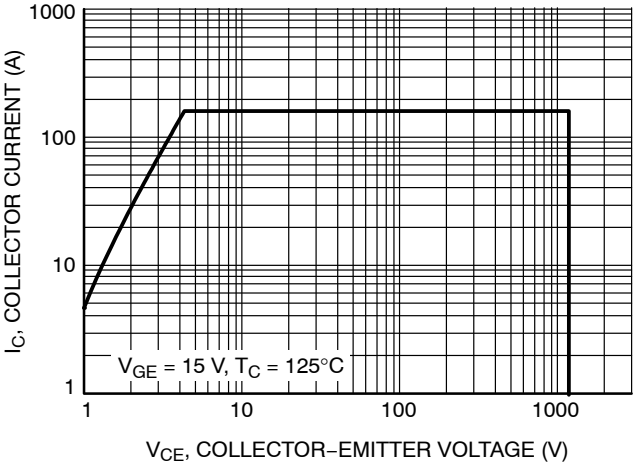


Figure 18. Reverse Bias Safe Operating Area

TYPICAL CHARACTERISTICS

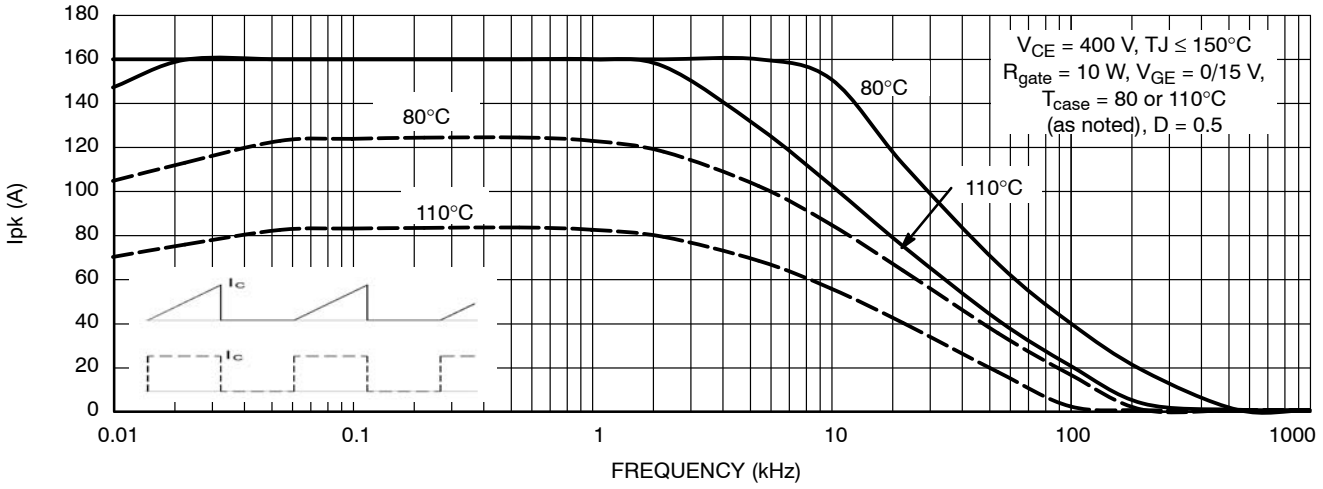
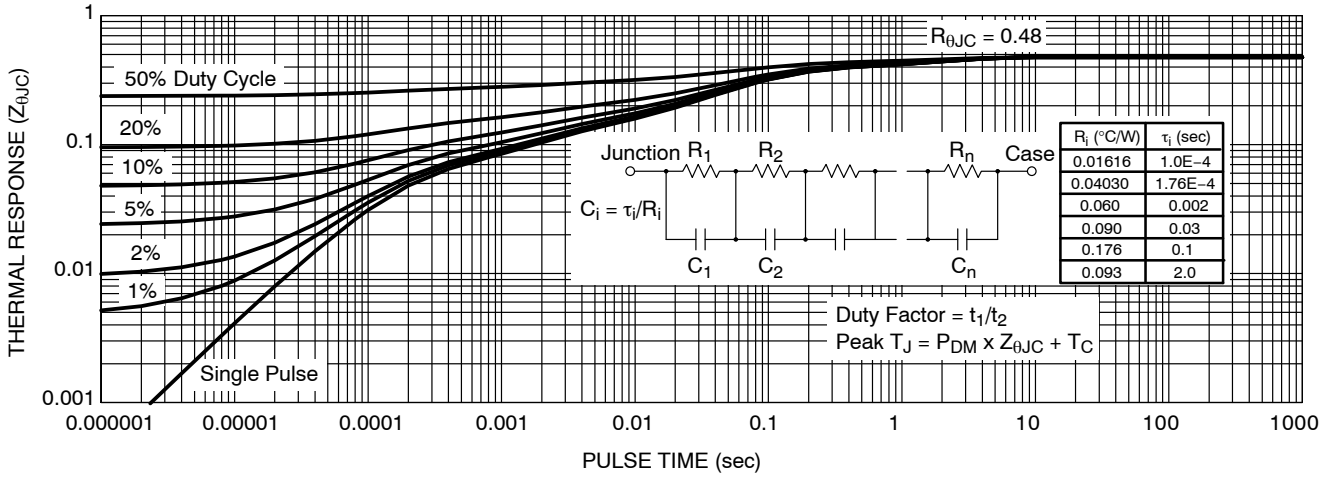
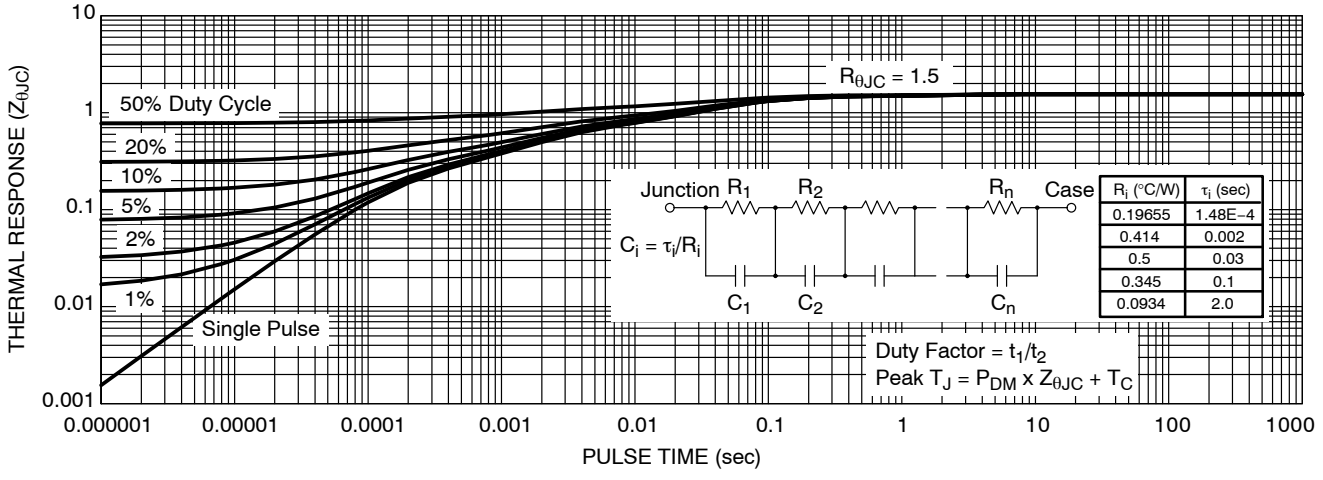


Figure 19. Collector Current vs. Switching Frequency



R_i (°C/W)	τ_i (sec)
0.01616	1.0E−4
0.04030	1.76E−4
0.060	0.002
0.090	0.03
0.176	0.1
0.093	2.0

Figure 20. IGBT Transient Thermal Impedance



R_i (°C/W)	τ_i (sec)
0.19655	1.48E−4
0.414	0.002
0.5	0.03
0.345	0.1
0.0934	2.0

Figure 21. Diode Transient Thermal Impedance

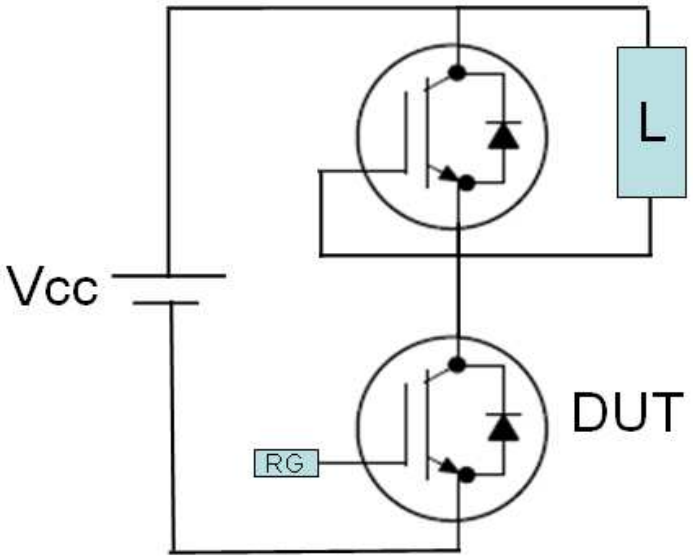


Figure 22. Test Circuit for Switching Characteristics

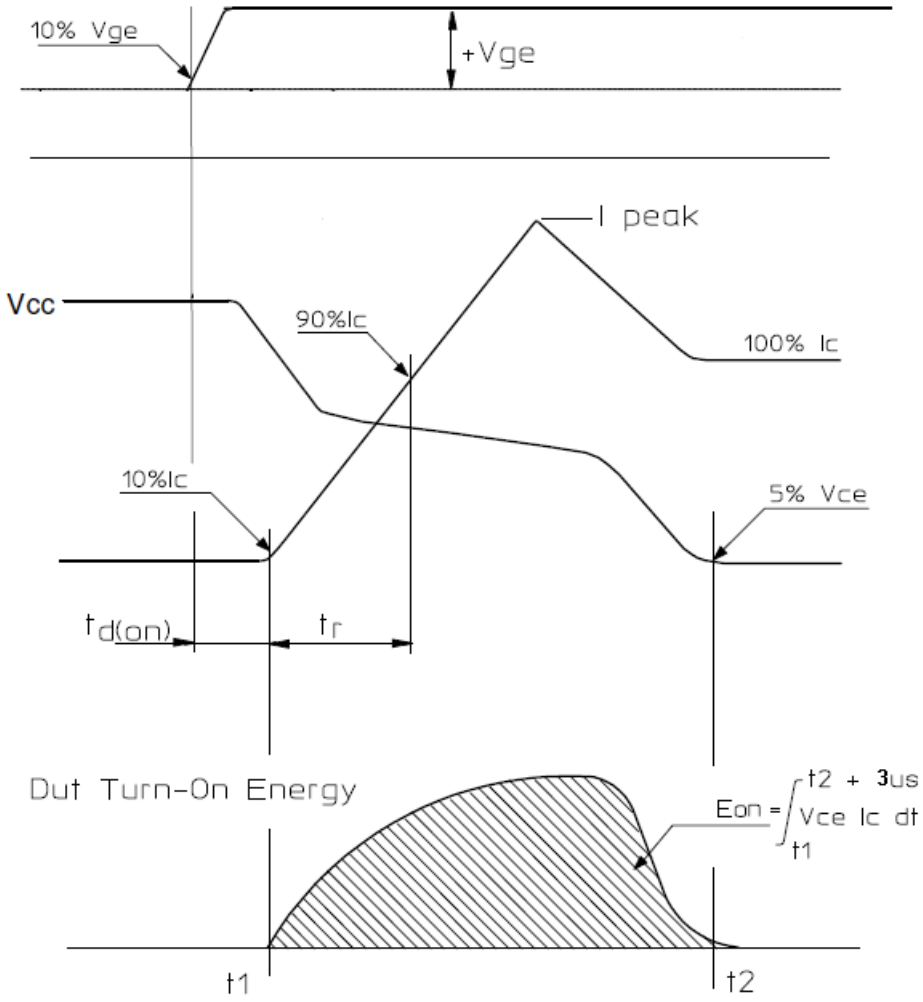


Figure 23. Definition of Turn On Waveform

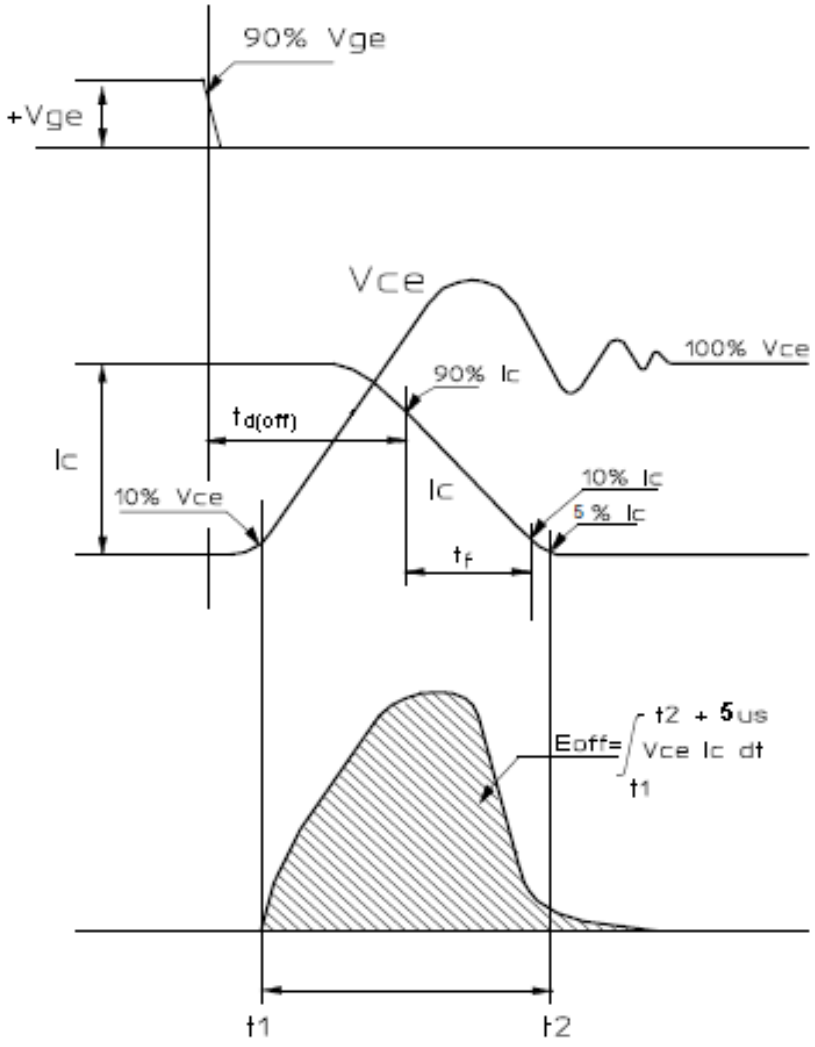
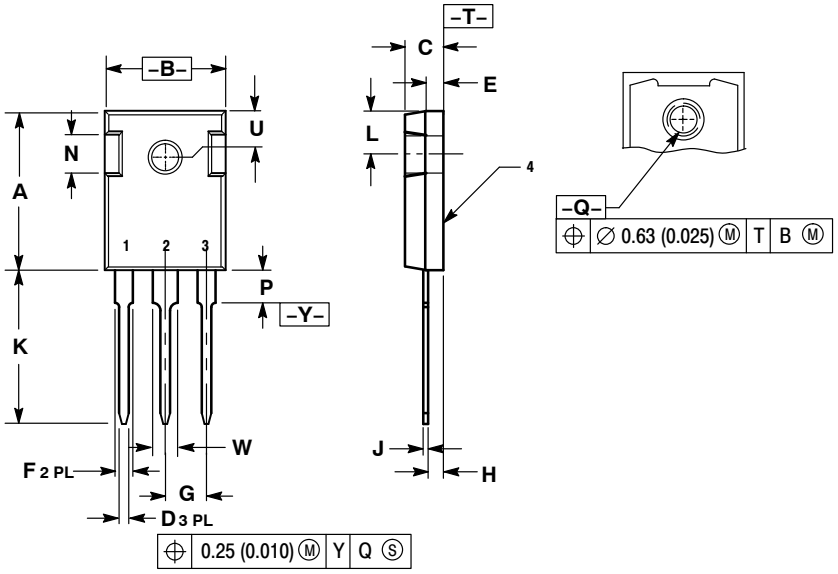


Figure 24. Definition of Turn Off Waveform

PACKAGE DIMENSIONS

TO−247
CASE 340L−02
ISSUE F



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	20.32	21.08	0.800	8.30
B	15.75	16.26	0.620	0.640
C	4.70	5.30	0.185	0.209
D	1.00	1.40	0.040	0.055
E	1.90	2.60	0.075	0.102
F	1.65	2.13	0.065	0.084
G	5.45 BSC		0.215 BSC	
H	1.50	2.49	0.059	0.098
J	0.40	0.80	0.016	0.031
K	19.81	20.83	0.780	0.820
L	5.40	6.20	0.212	0.244
N	4.32	5.49	0.170	0.216
P	---	4.50	---	0.177
Q	3.55	3.65	0.140	0.144
U	6.15 BSC		0.242 BSC	
W	2.87	3.12	0.113	0.123

STYLE 4:
PIN 1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

NGTB40N120FLW/D